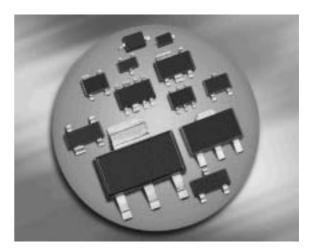


# Silicon Variable Capacitance Diode

- For VHF tuned circuit applications
- High figure of merit
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101





### BB439



Туре	Package	Configuration	<b>L</b> s(nH)	Marking
BB439	SOD323	single	1.8	white 2

#### **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit					
Diode reverse voltage	V <sub>R</sub>	28	V					
Peak reverse voltage	V <sub>RM</sub>	30						
( $R \ge 5 \mathrm{k} \Omega$ )								
Forward current	/ <sub>F</sub>	20	mA					
Operating temperature range		-55 125	°C					
Storage temperature	T <sub>stg</sub>	-55 150						

<sup>1</sup>Pb-containing package may be available upon special request



Parameter	Symbol	Values			Unit
		min.	typ.	max.	1
DC Characteristics					
Reverse current	I <sub>R</sub>				nA
V <sub>R</sub> = 28 V		-	-	20	
$V_{\rm R} = 28 \text{ V}, \ T_{\rm A} = 85 \ ^{\circ}\text{C}$		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		-	43	-	
$V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$		31.5	34.5	37.5	
$V_{R} = 3 \text{ V}, f = 1 \text{ MHz}$		26.5	29	31.5	
$V_{\rm R} = 25  {\rm V},  f = 1  {\rm MHz}$		4.3	5.1	6	
Capacitance ratio	C <sub>T2</sub> /C <sub>T25</sub>	6	6.9	8	
$V_{\rm R} = 2 \text{ V}, V_{\rm R} = 25 \text{ V}, f = 1 \text{ MHz}$					
Capacitance ratio	C <sub>T3</sub> /C <sub>T25</sub>	5	5.8	6.5	
$V_{\rm R} = 3 \text{ V}, V_{\rm R} = 25 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching <sup>1)</sup>	$\Delta C_{\rm T}/C_{\rm T}$	-	-	3	%
$V_{\rm R} = 3 \text{ V}, V_{\rm R} = 25 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	r <sub>S</sub>	-	0.35	0.5	Ω
V <sub>R</sub> = 10 V, <i>f</i> = 100 MHz					
Figure of merit	Q				
$V_{R} = 3 \text{ V}, f = 50 \text{ MHz}$		-	280	-	
$V_{\rm R} = 25 \text{ V}, f = 200 \text{ MHz}$		-	600	-	

# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

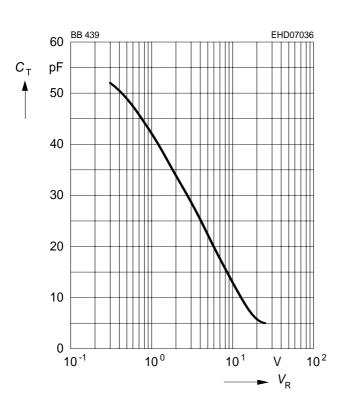
<sup>1</sup>For details please refer to Application Note 047.



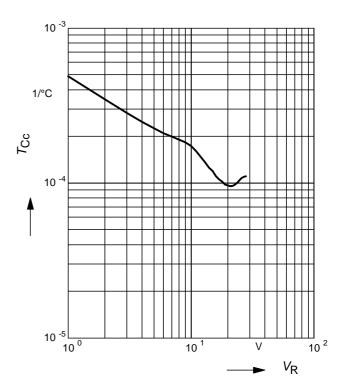
BB439...

**Diode capacitance**  $C_{\rm T} = f (V_{\rm R})$ 

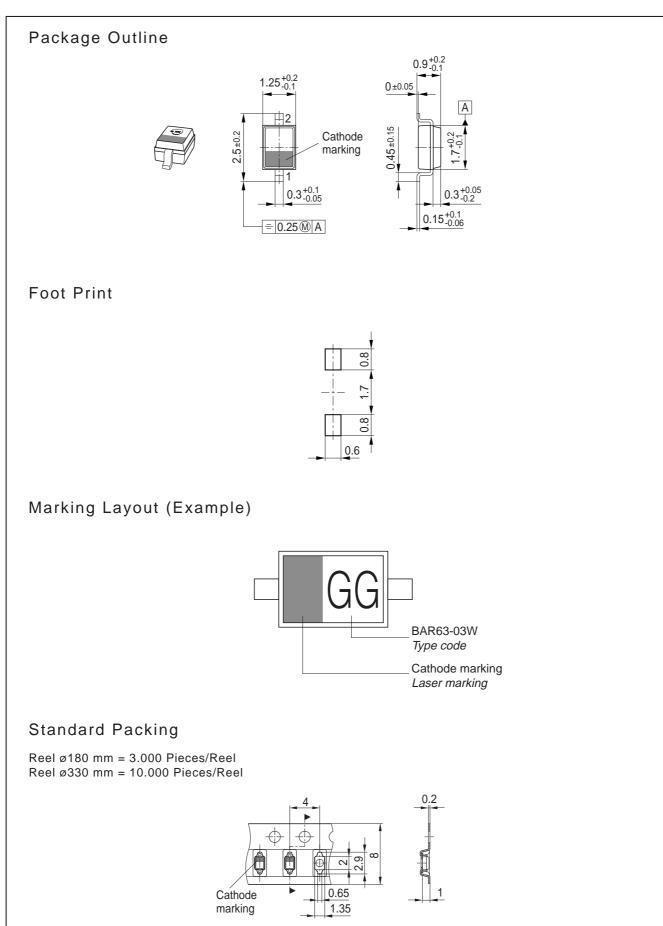
f = 1 MHz



Temperature coefficient of the diode capacitance  $T_{Cc} = f(V_R)$ 









Edition 2006-02-01 Published by Infineon Technologies AG 81726 München, Germany © Infineon Technologies AG 2007. All Rights Reserved.

# Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

## Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

## Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.